

IGBT-based High Voltage to Low Voltage DC/DC Converter for Electric and Hybrid Vehicles

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Abstract

The subject of this thesis is a high voltage (HV) to low voltage (LV) DC/DC converter in hybrid (HEVs) and electric vehicles (EVs). The focus is on use of an IGBT-based zero voltage transition (ZVT) phase shift (PS) full bridge (FB) topology for this application. Not only the high switching frequency is a challenge when designing the IGBT-based ZVT PS FB converter, but also the wide input voltage range and wide range of load currents during operation of the converter pose additional difficulty for its design and operation. In order to use the available energy of the HV battery of (H)EVs more efficiently, cost-effective loss reduction is one of the main objectives in the development of automotive HV to LV DC/DC converters, and therefore the significant portion of this work is focused in that direction.

The research starts with the question if improved, trench fieldstop IGBT switches with tailless behavior, optimized for high frequency switching ('high speed' IGBTs), have potential to substitute superjunction MOSFETs that are nowadays commonly used at HV-side of the DC/DC converter at switching frequency of 100kHz. The efficiency of the IGBT-based converter is analyzed in detail in order to identify the most critical loss mechanisms and to propose efficiency improvement methods accordingly. Furthermore, one of the issues due to the required wide input and output voltage range is the voltage overshoot during turn-off of rectifier switches. A model is developed and experimentally validated for three different rectifier topologies to simulate turn-off voltage waveforms. Based on this model, the choice of the rectifier and its impact on the overall converter operation is discussed. In addition, design considerations to improve efficiency of the ZVT PS FB converter that were successfully applied in MOSFET-based designs are analyzed in the converter designed with 'high speed' IGBTs. The focus is on use of an external inductor to eliminate turn-on losses in the lagging leg of the HV side H bridge, and capacitive snubbers to reduce the turn-off losses. The effect of such additional components on switching losses of IGBTs and overall converter efficiency is analyzed. The results showed that the advantage of modern IGBTs over superjunction MOSFETs and older IGBT technologies is their optimal performance without external inductive and capacitive components. Thanks to their reduced turn-off losses, and at the same time low turn-on losses, the loss of ZVT in the lagging leg is not anymore critical to converter's efficiency. Since the investigated approaches are not efficient in IGBT-based ZVT PS FB in (H)EVs, and different approaches had to be developed to further improve the efficiency.

Finally, to offer a solution for the problem of reduced efficiency due to the wide input voltage range, a new efficiency optimized single-stage reconfigurable topology is proposed. The proposed topology solves the problem of reduced converter efficiency in the upper range of HV battery voltages by adapting the transformer turns ratio depending on the input voltage. The topology is based on the ZVT PS FB converter that is during its operation, depending on the instantaneous value of battery voltage, reconfigured into a push-pull converter. The ZVT PS FB - the more efficient configuration covers upper range of input voltages whereas the hard-switching push-pull - the less efficient configuration covers the lower, less significant range. The ZVT PS configuration, due to tighter voltage range and more suitable transformer turns ratio, operates with reduced turn-off losses, significantly decreased circulating current in the freewheeling period as well as improved efficiency of the rectifier stage. The point of reconfiguration is chosen to maximize the average efficiency according to the histogram of HV battery voltage during a typical driving cycle. The proposed reconfiguration principle is

also applicable to the rectifier stage at the LV side of the same converter. Operation of the proposed converter and the efficiency improvement are validated experimentally.

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Contents

List of Figures	vii
List of Tables	xvii
1 Introduction	1
1.1 Background	1
1.1.1 Role of HV to LV DC/DC Converter in (H)EVs	1
1.1.2 Converter Specification	2
1.1.3 Converter Topology	4
1.2 Motivation	7
1.2.1 Application of Modern IGBT Technologies at High Switching Frequencies	7
1.2.2 Operation of DC/DC Converter in Wide Input Voltage Range Conditions	9
1.3 Thesis Objectives, Contribution and Organization	10
2 IGBT-based ZVT Phase Shift Converter	15
2.1 Application of 'High Speed' IGBTs at Switching Frequencies in Range of 100 kHz	15
2.1.1 Turn-off Switching Characteristic and Energy Losses	16
2.1.2 Output Characteristic	19
2.1.3 Output Capacitance and Energy of ZVT Transition	20
2.1.4 Turn-on and Hard Diode Commutation	21
2.1.5 Summary	23
2.2 Zero Voltage Transition Phase Shift DC/DC Converter	24
2.2.1 Operation Principle	24
2.2.2 Loss Modeling and Analysis	27

CONTENTS

2.2.2.1	Loss Model Parameterization and Parameters' Temperature Dependence	28
2.2.2.2	Power Losses and Efficiency: Experimental Measurements and Model Validation	34
2.2.2.3	Loss Distribution in Prototype Converter	35
2.3	Rectifier Topology Selection	39
2.3.1	Design Parameters and Operation Principle of Different Rectifier Topologies	40
2.3.2	Rectifier Overvoltage Peaks	44
2.3.3	Predictive Model of Rectifier Overvoltage Peaks and Experimental Validation	44
2.3.4	Model Verification and Discussion	48
2.3.5	Efficiency Comparison	50
2.4	Summary	53
3	Switching Behavior of 'High Speed' IGBTs in ZVT Phase Shift Converter	55
3.1	Effect of Capacitive Snubbers on IGBT's Turn-off Losses in the Leading Leg	57
3.1.1	Experimental Results	59
3.1.2	Analysis of Tail Bump of 'High Speed' IGBTs Caused by C_{ext}	59
3.1.3	Effect on Efficiency	63
3.2	Effect of External Inductor on IGBT's Switching Losses in Lagging Leg	64
3.2.1	Zero Voltage Transition in Lagging Leg	64
3.2.2	Turn-On Losses in Lagging Leg Transition	66
3.2.3	Turn-Off Losses in Lagging Leg Transition	69
3.2.4	Conduction Losses in Freewheeling	72
3.2.5	Effect on Efficiency	72
3.3	Summary	73
4	Single-Stage Reconfigurable ZVT Phase Shift Converter Optimized for Wide Input Voltage Range Operation	77
4.1	Operating Voltages of HV Battery	78
4.1.1	Battery Electric Vehicles	79
4.1.2	Plug-in Hybrid Electric Vehicles	79

4.2	Proposed Reconfigurable Topologies	81
4.3	Implementation of Proposed Topologies	83
4.3.1	Reconfiguration at LV Side	83
4.3.2	Reconfiguration at HV Side	85
4.4	Model-based Evaluation of Potential for Efficiency Improvement	86
4.5	Design Procedure for Proposed HV-side Reconfigurable Converters for Operation in BEVs	91
4.6	Experimental Validation of HV-Side Reconfigurable Converter	93
4.7	Discussion	96
4.7.1	Loss Reduction at Turn-off and in Freewheeling Period	96
4.7.2	Choice of Rectifier Switches	99
4.7.3	Losses in Passive Components	101
4.7.4	Operation of Push-pull Configuration	102
4.7.5	Potential for Further Improvements	103
4.8	Summary	104
5	Conclusion	107
6	Appendices	111
6.1	Loss Modeling of ZVT Phase Shift Full Bridge DC/DC Converter	111
6.1.1	Losses of HV-side Switches	111
6.1.2	Losses in LV-side Rectifier	116
6.1.3	Losses in Power Transformer and Output Filter	119
6.1.4	Losses in LV-side Printed Circuit Board	120
6.2	Loss Modeling of Push-pull DC/DC Converter	121
6.2.1	Losses in HV-side Switching Components	121
6.2.2	Losses in LV-side rectifier	124
6.2.3	Losses in Power Transformer, Output Filter and in Printed Cir- cuit Board at LV Side	126
6.3	Description of Converter Prototype	126
6.3.1	Phase Shift Full Bridge DC/DC Converter	126
6.3.2	Reconfigurable Converter	126
References		129

CONTENTS

List of Figures

1.1	Supply system of 14 V power net in (a) conventional ICE driven vehicles and (b) in (H)EVs.	2
1.2	ZVT PS FB DC/DC topology for (H)EVs.	5
1.3	Simplified block diagram of HV to LV DC/DC converter.	6
2.1	Pulse test-setup (single/double) used for characterization of IGBT(MOSFET) switches.	16
2.2	Turn-off switching waveforms at 25 A, 300 V at $T_j = 150^\circ C$ of (a) high voltage MOSFET, (b) standard trench fieldstop IGBT and (c) 'high speed' IGBT.	17
2.3	Measured turn-off energy losses as a function of collector (drain) current for 'high speed' IGBT and high voltage MOSFET at (a) $T_j = 25^\circ C$ and (b) $T_j = 150^\circ C$ at 200 V, 300 V and 400 V turn-off voltage.	18
2.4	Output characteristic of 'high speed' IGBT 3 and high voltage MOSFET at (a) $T_j = 25^\circ C$ and (b) $T_j = 150^\circ C$	19
2.5	Standard experimental setup for C_{oss} measurement.	20
2.6	Proposed experimental setup used to estimate the energy required to achieve ZVT in one leg of H-bridge.	21
2.7	Waveforms measured in proposed setup for ZVT energy estimation: green trace - V_{ge} , violet trace - $I_{L_{aux}}$, brown trace - V_{ce} , yellow - calculated required energy.	22
2.8	(a) Estimated energy required for ZVT in one leg. (b) Estimated transition times.	23

LIST OF FIGURES

2.9 Waveforms of hard diode commutation of (a) 'rapid emitter controlled' diode antiparallel to 'high speed' IGBT and (b) fast recovery body diode of HV MOSFET. Operating point: $I_{c,turnoff} = 25 A$, $V_{in} = 300 V$ 24

2.10 Operating states of ZVT PS FB converter from Fig. 1.2 with active H-bridge rectifier: (a) power transfer (positive magnetization of the transformer core) (b) leading leg transition (c) freewheeling period and (d) lagging leg transition. The power flow in each domain of one half of T_s is presented with dotted line. In the other half of T_s , the order of the operating states is the same, except the fact that the transformer core is magnetized in the opposite direction so that the corresponding switches conduct. 25

2.11 (a) Transformer primary winding current, (b) voltages over synchronous rectifiers (SRs), (c) currents of SRs and (d) switching patterns for primary and secondary switches. 26

2.12 Estimation of junction temperature T_j of the switches in HV-side H-bridge in the steady state operation: (a) switch S_1 (symmetric to S_3), (b) switch S_2 (symmetric to S_4), and (c) freewheeling diode D_2 (symmetric to D_4 , while diodes D_1 and D_3 do not conduct current during normal operation). 30

2.13 Temperature dependence of $r_{ds,on}$ of 80 V MOSFET (IPB019N08N3 G) used in the rectifier of the converter prototype. The data presented are provided in the manufacturer data sheet. 31

2.14 Core losses as a function of the core temperature and applied flux density for the transformer core described in Section 2.2.2.1 (characterization data provided by the manufacturer, obtained with the sinusoidal voltage excitation of 100 kHz, where the given flux density corresponds to the peak flux density). 32

2.15 Efficiency of 'high speed' IGBT-based converter over the range of input voltages (200 V, 275 V and 350 V). Efficiency curves obtained from prototype measurements are in solid line, and calculated data are presented by markers. 34

2.16	Loss distribution over HV-side switches, LV-side switches and passives based on the parameterized loss model for: (a) $V_{in} = 200\text{ V}$ (b) $V_{in} = 275\text{ V}$ (c) $V_{in} = 350\text{ V}$. Losses are presented cumulatively (stacked area chart) and their sum is compared to the percentage of total losses obtained experimentally.	36
2.17	Comparison of power losses at three different V_{in} values (200 V, 275 V and 350 V): (a) losses at HV-side switches (b) losses at LV-side switches and (c) losses at passives (transformer, LC filter, PCB). Losses are presented one beside the other so that their difference is clearly visible (layered area chart).	37
2.18	Distribution of losses on HV-side switches (conduction losses of IGBTs, diodes and switching losses of IGBTs) for: (a) $V_{in} = 200\text{ V}$ (b) $V_{in} = 275\text{ V}$ (c) $V_{in} = 350\text{ V}$. Losses are presented cumulatively (stacked area chart).	38
2.19	Distribution of losses caused by passive components and LV-side switches in the converter at $V_{in} = 275\text{ V}$. These losses are nearly independent on V_{in} . Losses are presented cumulatively (stacked area chart).	39
2.20	Investigated rectifier topologies: (a) full wave rectifier (b) bridge rectifier and (c) current doubler.	40
2.21	Simulated current waveforms in: (a) full wave rectifier (b) bridge rectifier and (c) current doubler. $I_{C_{out}}$ is the current in the filter capacitor, $I_{tr,sec}$ is the current in secondary winding, $I_{tr,prim}$ is the current in secondary winding and I_{SR1}/I_{SR2} are currents of LV-side MOSFETs.	42
2.22	Dependence of $R_{ds,on}$ on V_{br} of Infineon's <i>OptiMOSTM</i> family in a D2PAK package (source : www.infineon.com , released product, October 2011).	43
2.23	Functional (left) and equivalent (right) circuit of (a) full wave rectifier (b) bridge rectifier and (c) current doubler during the turn-off transition of one switch.	45
2.24	Mathematical model of rectifier switch transition from conducting to non-conducting state.	46
2.25	Simulation of voltage overshoot waveforms for three different rectifier topologies at (a) $V_{in} = 200\text{ V}$ and (b) $V_{in} = 400\text{ V}$	48

LIST OF FIGURES

2.26 Dependency of voltage overshoot on C_{oss} and L_{leak} : (a) trend of $V_{C_{oss,max}}$ and (b) trend of f_{osc} . Steady state blocking voltage is assumed to be 40 V. 49

2.27 Experimental verification of the model of voltage overshoot for (a) full wave rectifier (200 V 8:1:1) (b) current doubler (200 V 7:1) and (c) full bridge rectifier (200 V 8:1) 50

2.28 The comparison of efficiency of ZVT PS converter with the full wave rectifier to the full bridge rectifier at (a) 160 V and (b) 300 V. 52

3.1 ZVT PS FB DC/DC converter with additional components for efficiency improvement: external inductor L_{ext} in the lagging leg and external capacitors C_{ext} in the leading leg. 57

3.2 Illustration of turn-off event of a MOSFET in the leading leg (a) without capacitive snubber compared to (b) the case with capacitive snubber (The same behavior assumed for tailless 'high speed' IGBTs). 58

3.3 Leading leg turn-off transition in reference to the rest of T_s 59

3.4 Measured turn-off waveforms of 'high speed' IGBT for three different values of $C_{ext}@T_{vj} = 25^\circ C$: left side - $V_{in} = 200 V$, $I_{c,turn-off} = 10 A$, right side - $V_{in} = 200 V$, $I_{c,turn-off} = 20 A$, (a) no C_{ext} , (b) $C_{ext} = 500 pF$, (c) $C_{ext} = 2 nF$, and (d) turn-off loss energy E_{off} 60

3.5 Comparison of the tail current and turn-off loss energies of 'high speed' IGBT for (a) $T_{vj} = 25^\circ C$ and (b) $T_{vj} = 150^\circ$. Operating point: $I_{c,turnoff} = 25 A$, $V_{in} = 300 V$, no C_{ext} applied. 61

3.6 Turn-off of IGBT switch with (a) $C_{ext} = 500 pF$ at $T_{vj} = 25^\circ C$, (b) $C_{ext} = 500 pF$ at $T_{vj} = 150^\circ C$, (c) comparison of E_{off} with $C_{ext} = 500 pF$ for two different T_{vj} , (d) $C_{ext} = 2 nF$ at $T_{vj} = 25^\circ C$, (f) $C_{ext} = 2 nF$ at $T_{vj} = 150^\circ C$, and (e) comparison of E_{off} with $C_{ext} = 2 nF$ for two different T_{vj} . Operating point: $I_{c,turnoff} = 10 A$, $V_{in} = 200 V$. . . 62

3.7 Phases in the turn-off of 'high speed' IGBT with parallel capacitor when a bump in the tail current occurs (illustration). 63

3.8	Efficiency comparison (at $T_h = 25^\circ C$, auxiliary supply ≈ 8 W const. not included) without capacitive snubber and with two values of capacitive snubber ($C_{ext} = 2$ nF and $C_{ext} = 500$ pF) at (a) $V_{in} = 200$ V and (b) $V_{in} = 300$ V. I_{load} of 150 A corresponds to the $I_{c,turn-off}$ of 20 A, and I_{load} of 75 A corresponds to the $I_{c,turn-off}$ of 10 A.	65
3.9	Lagging leg transition in reference to the rest of T_s	66
3.10	Turn-on of the switch in the lagging leg when ZVT is achieved (gate voltage occurs when V_{ce} is already 0 V, operating point: $V_{in} = 200$ V, $I_{out} = 115$ A, $L_{ext} = 2.2\mu H$, $L_{leak} = 1.3\mu H$).	67
3.11	Turn-on of the switch in the lagging leg when ZVT is not achieved (gate voltage occurs while V_{ce} is equal to V_{in} , operating point: $V_{in} = 200$ V, $I_{out} = 115$ A, $L_{ext} = 0\mu H$, $L_{leak} = 1.3\mu H$	68
3.12	Turn-off of the switch in lagging leg when ZVT is not achieved. Operating point: $V_{in} = 200$ V, $I_{out} = 115$ A, $L_{ext} = 0\mu H$, $L_{leak} = 1.3\mu H$. Red trace is the voltage over the switch that turns off, and blue trace is the current of the primary transformer winding that charges/discharges the capacitances of the lagging leg (thus it does not correspond to the switch current).	70
3.13	Primary winding current during the lagging leg transition when $L_{ext} = 2.2\mu H$ applied in addition to $L_{leak} = 1.3\mu H$ of primary winding (black trace) and when no L_{ext} applied so that only L_{leak} is present during transition (blue trace). Operating point: $V_{in} = 200$ V, $I_{Lout} = 115$ A, $L_{ext} = 0\mu H$, $L_{leak} = 1.3\mu H$	71
3.14	(a) Currents $I_{c,turn-off}$ with ZVT achieved (dotted line) and ZVT not achieved (solid line) at $V_{in} = 200$ V (markers - calculated, lines - measured). (b) Voltages $V_{ce,turn-off}$ of S_1 at $V_{in} = 200$ V when ZVT achieved (dotted line) and not achieved (solid line).	71
3.15	(a) Comparison of switching energies during the lagging leg transition for cases with and without L_{ext} . This transition occurs twice per switching period. ($V_{in} = 200$ V). (b) Comparison of conduction losses in primary winding circuit during the freewheeling period ($V_{in} = 200$ V).	72

LIST OF FIGURES

3.16 Efficiency comparison of 'high speed' IGBT-based design of ZVT PS FB converter (at $T_h = 25^\circ C$, auxiliary supply $\approx 8 W$ const. not included) without and with two different values of L_{ext} . The best overall efficiency was achieved without L_{ext} , despite the fact that ZVT was not achieved over the presented operating range. 73

4.1 (a) Battery voltage (b) SoC (c) battery discharge current and (d) histogram of HV battery voltages during one discharge cycle of Li-Ion battery in an EV obtained using FTP75 driving cycle data. 80

4.2 Illustration of SoC in a PHEV that initially operates in the charge depleting mode, and after reaching certain value of SoC, it continues its operation in charge sustaining mode. 81

4.3 (a) LV-side reconfigurable topology based on ZVT PS converter. (b) Configuration with full bridge rectifier for lower V_{in} range (switch in position 1). (c) Configuration with full wave rectifier for higher V_{in} range (switch in position 2). 82

4.4 (a) HV-side reconfigurable topology based on ZVT PS converter (b) Push-pull configuration for lower V_{in} range (switch in position 1). (c) Full bridge configuration for higher V_{in} range (switch in position 2). . . 84

4.5 Proposed implementation of two-position switch in LV reconfigurable topology (SR_5 conducts in the full wave rectifier configuration and SR_6 in the full bridge rectifier configuration. Both switches do not exhibit repetitive switching losses, only conduction losses.). 85

4.6 Proposed implementation of two-position switch in HV reconfigurable topology (S_{add} conducts in push-pull configuration and D_{add} in ZVT PS FB configuration. Both switches do not exhibit repetitive switching losses, only conduction losses.). 86

4.7 Two different configurations of proposed topology: (a) ZVT PS configuration in upper range of V_{in} and (b) push-pull configuration in lower range of V_{in} with corresponding primary winding currents and gate signals. Gate drive signals for push-pull operating mode can be derived from those for ZVT PS FB configuration using 2 AND logic gates. . . . 87

4.8	Model-based estimation of efficiency over different V_{in} values of converter designed according to specification from Table 1.1 in case of (a) standard ZVT PS FB, (b) LV reconfigurable converter, and (c) HV reconfigurable converter.	89
4.9	Flowchart of design procedure for reconfigurable converter.	92
4.10	(a) Voltage-weighted average efficiency of the proposed converter as a function of chosen V_{reconf} . (b) Expected increase in the average efficiency when V_{reconf} is chosen as 300 V (detail from the plot (a)).	93
4.11	Family of efficiency curves (prototype measurements) of (a) the conventional ZVT PS FB with the transformer turns ratio of 10:1 and (b) the proposed reconfigurable converter with the transformer turns ratio of 10:10:1 and $V_{reconf} = 300$ V.	94
4.12	Voltage-weighted average efficiency of the proposed converter compared to the conventional one calculated based on prototype measurements from Fig. 4.11.	95
4.13	Experimentally obtained waveforms of (a) the primary winding current $I_{t,prim}$ and (b) voltage over an IGBT switch V_{ce} in the proposed (blue trace) and the standard converter prototype (red trace). All waveforms are measured in the same operating point with $V_{in} = 350$ V and $I_{load} = 75$ A. Proposed converter operates in ZVT PS FB configuration since $V_{in} > V_{reconf}$	96
4.14	(a) RMS currents of switches in the HV-side H-bridge in the proposed (dashed line) and in the standard converter (solid line) over the range of load currents. (b) Total losses of switches in the HV-side H-bridge in the conventional (blue line) and proposed converter (green line) as well as on D_{add} in the proposed converter (red line). (c) Efficiency difference of switches in the HV-side H-bridge. The data is presented over the range of load currents at $V_{in} = 350$ V where the proposed converter operates in ZVT PS FB configuration.	97

LIST OF FIGURES

4.15 The comparison of losses in the reconfigurable (area in the front) and the standard ZVT PS FB converter (area in the background) at $V_{in} = 350 V$ at (a) HV-side switches (b) LV-side switches and (c) passive elements (transformer, output filter and losses in PCB). Losses are presented one beside the other so that their difference is clearly visible (layered area chart). 98

4.16 Waveforms of the proposed converter in the push-pull configuration at $V_{in} = 250 V$ and $I_{load} = 75 A$: (a) the primary winding current $I_{t,prim}$ (b) voltage over an IGBT switch V_{ce} and (c) gate drive voltage of the switch V_{ge} 100

4.17 Some improvements of ZVT PS FB topology recently proposed in the literature (a) (1), (b) (2), (c) (3), and (d) (4). 106

6.1 Current waveform of transformer primary winding over one T_s with slopes used in Eqs. (6.1) to (6.3) and corresponding gate drive signals of HV-side H-bridge. 112

6.2 Current waveforms of the rectifier switches over one T_s (blue, solid line - SR_1 and SR_3 , green, dotted line - SR_2 and SR_4) and corresponding gate drive signals. Slopes used in Eqs. (6.29) to (6.33) are marked. . . . 116

6.3 Model of resistances of traces in the LV-side PCB used for calculation of conduction losses inside the board. The model is valid for the full bridge rectifier. The position of resistances is presented on the illustration of the board. 121

6.4 Model of resistances of traces in the LV-side PCB used for calculation of conduction losses inside the board. The model is valid for (a) full bridge rectifier (b) full wave rectifier and (c) current doubler. 122

6.5 Current waveforms of HV-side switches over one T_s (blue, solid line - SR_1 , green, dotted line - SR_2) and corresponding gate drive signals. Slope used in Eq. (6.51) is marked. 123

6.6 Current waveforms of the rectifier switches over one T_s (blue, solid line - SR_1 and SR_3 ; green, dotted line - SR_2 and SR_4) and corresponding gate drive signals. Slopes used in Eqs. (6.62) to (6.63) are marked. . . . 124

6.7 Photo of converter prototype (front side). 127

6.8 Photo of converter prototype (HV side, back). 128

LIST OF FIGURES

List of Tables

1.1	Characteristics of HV to LV DC/DC converter in (H)EVs.	3
2.1	Transformer turns ratio calculation.	41
2.2	Circuit parameters and operating conditions used in the developed model. 47	
3.1	Expected $V_{ce,turn-off}$ and $E_{off,C_{ext}}$ with 2 nF external capacitive snubber. $E_{off,C_{ext}}$ shows the expected reduction compared to design without C_{ext}	58
3.2	Loss mechanisms in IGBT-based converter affected by additional L_{ext}	74
4.1	Calculated design parameters : conventional vs. proposed topology with $V_{reconf} = 300$ V for the converter specification from Table 1.1.	89
6.1	Conduction periods and switching transitions of HV-side switches in one T_s	112
6.2	Conduction periods and transitions of LV-side switches in one T_s in case of ZVT PS FB converter.	117
6.3	Conduction periods and transitions of LV-side switches in one T_s in case of push-pull converter.	125
6.4	Prototype description.	127
6.5	Additional and modified components in the prototype converter used to enable reconfiguration.	128

LIST OF TABLES

Commonly Used Symbols of Physical Properties

Symbol	Unit	Description
B	T	Flux Density
C	F	Capacity
C_{oss}	F	MOSFET's Output Capacitance
C_{oes}	F	IGBT's Output Capacitance
D	-	Duty Cycle
ΔT_j	K	Junction Temperature Ripple
dv/dt	V/s	Slope of Voltage Rise
di/dt	A/s	Slope of Current Rise
E	Ws	Energy
η	%	Efficiency

LIST OF TABLES

f	Hz	Frequency
I	A	Current
L	H	Inductance
n	-	Transformer Turns Ratio
P	W	Power
R	Ω	Resistance
T_j	K	Junction Temperature
T_{vj}	K	Virtual Junction Temperature
T_a	K	Ambient Temperature
T_h	K	Heatsink Temperature
T_c	K	Case Temperature
T_s	s	Switching Period
t	s	Time
t_d	s	Dead Time
V	V	Voltage

LIST OF TABLES

Indices

Index	Description
<i>add</i>	additional
<i>aux</i>	auxiliary
<i>ave</i>	average
<i>BD</i>	body diode
<i>bat</i>	battery
<i>block</i>	blocking
<i>CD</i>	current doubler
<i>ce</i>	collector to emitter
<i>copp</i>	copper
<i>D</i>	diode

LIST OF TABLES

d_{loss}	loss of duty cycle
ds	drain to source
ESR	equivalent series resistance
FB	full bridge rectifier
frw	freewheeling period
FW	full wave rectifier
ge	gate to emitter
in	input
k	coefficient
lag	lagging leg
$lead$	leading leg
$leak$	leakage
min	minimum
max	maximum
nom	nominal

<i>off</i>	turn-off
<i>on</i>	on-state
<i>out</i>	output
<i>prim</i>	primary
<i>pt</i>	power transfer
<i>reconf</i>	reconfiguration
<i>ref</i>	reference
<i>res</i>	resonant
<i>RMS</i>	effective
<i>S</i>	switch
<i>SR</i>	synchronous rectifier
<i>sat</i>	saturation
<i>sec</i>	secondary
<i>t</i>	transformer